

ABSTRACT

SUBSTRATE PROCESSING METHOD

There is provided a substrate processing method, in which a throughput can be improved even in case the time for recovery processing for restoring the state of a processing chamber is longer than the time for predetermined processing to be performed in the processing chamber. Substrates are alternately transferred to two processing chambers C, D, and the same film forming processing is performed on the substrates in the processing chambers C, D in parallel with each other. When the number of substrates processed in the processing chamber C has reached a predetermined number (11 substrates), dummy sputtering processing in the film forming chamber C is started and also 23rd – 25th substrates of the first lot are transferred to the film forming chamber D to thereby perform film forming processing until the dummy sputtering processing is finished. When the dummy sputtering processing in the film forming chamber C has been finished, dummy sputtering processing is started in the film forming chamber D and also the 1st – 3rd substrates of the second lot are transferred to the film forming chamber C to thereby perform film forming processing until the dummy sputtering processing is finished. When the dummy sputtering processing in the film forming chamber D has been finished, alternate transferring of substrates is resumed.

Figure 3